

N-channel 100 V 37.5 mΩ logic level MOSFET in LFPAK56 1 May 2013

Product data sheet

1. **General description**

Logic level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in LFPAK56 package. This product has been designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses •
- Suitable for logic level gate drive
- LFPAK56 package is footprint compatible with other Power-SO8 types •
- Qualified to 175 °C •

Applications 3.

- DC-to-DC converters •
- Load switch
- TV power supplies

Quick reference data 4.

Table 1. Qu	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	30	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	94.9	W
Static charac	cteristics	·	1	1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12		-	-	103.5	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>		-	30.2	37.5	mΩ
Dynamic cha	aracteristics	I	1				
Q _{G(tot)}	total gate charge	V _{GS} = 5 V; I _D = 5 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 14; Fig. 15</u>		-	21.6	-	nC
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 5 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	8.3	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 30 \text{ A}; \ V_{sup} \leq 100 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 3 \end{array}$		-	-	45.1	mJ

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate	ប្រុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package	Package					
	Name	Description	Version				
PSMN038-100YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN038-100YL	038100

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

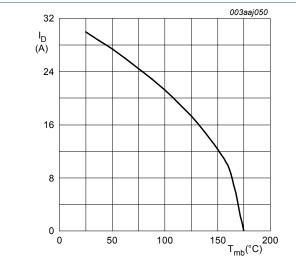
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	30	А
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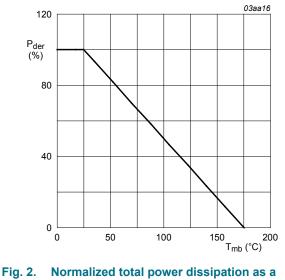
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Symbol	Parameter	Conditions	Min	Max	Unit
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	21.3	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	94.9	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dra	in diode		I		
I _S	source current	T _{mb} = 25 °C	-	79	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	120	А
Avalanche	ruggedness		I		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_{D} = 30 \text{ A}; V_{sup} \le 100 \text{ V}; R_{GS} = 50 \Omega;$ $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; \text{ unclamped};$ Fig. 3	-	45.1	mJ





 $V_{GS} \ge 10V$

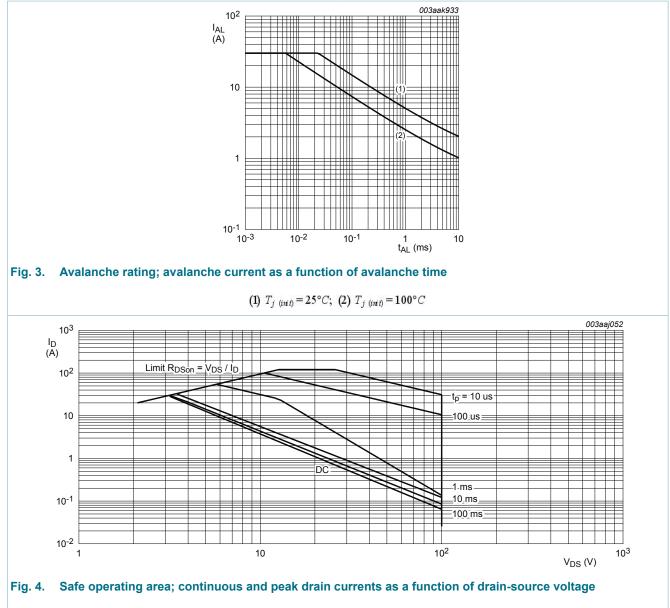


function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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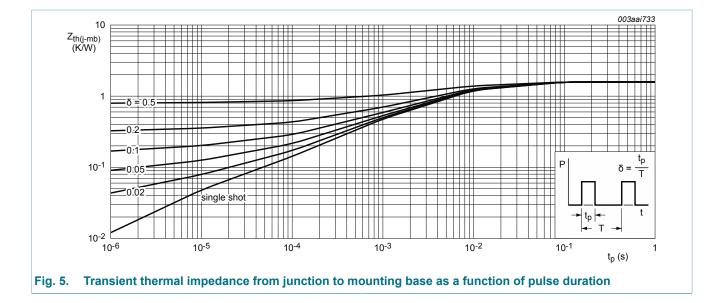


 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	1.44	1.58	K/W	

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.5	-	-	V
I _{DSS} drain leakage	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	31.3	38	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12	-	-	103.5	mΩ
		V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C; Fig. 12	-	30.2	37.5	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 13; Fig. 12	-	-	105	mΩ
R _G	gate resistance	f = 1 MHz	-	1.64	_	Ω

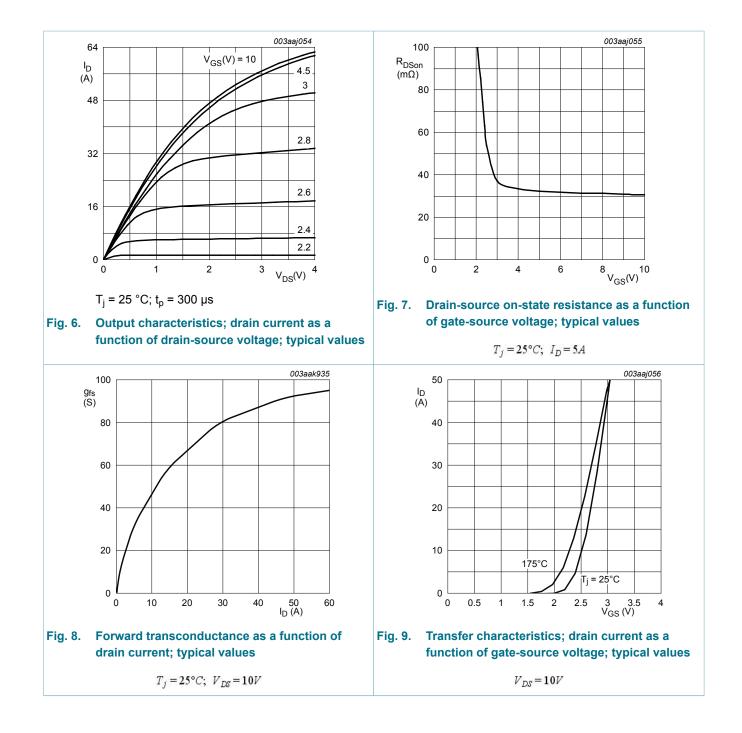
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14; Fig. 15</u>	-	39.2	-	nC
		I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 14; Fig. 15</u>	-	21.6	-	nC
Q _{GS}	gate-source charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	3.8	-	nC
Q _{GD}	gate-drain charge		-	8.3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	2.7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	1.1	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 5 A; V _{DS} = 80 V; T _j = 25 °C; Fig. 14; Fig. 15	-	2.3	-	V
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 16</u>	-	1905	-	pF
C _{oss}	output capacitance		-	137	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 10 Ω; V _{GS} = 5 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	18	-	ns
t _{d(off)}	turn-off delay time		-	31	-	ns
t _f	fall time	-	-	18	-	ns
Source-dra	in diode	· · · · · ·	I	I	1	_
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	31	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	44	-	nC

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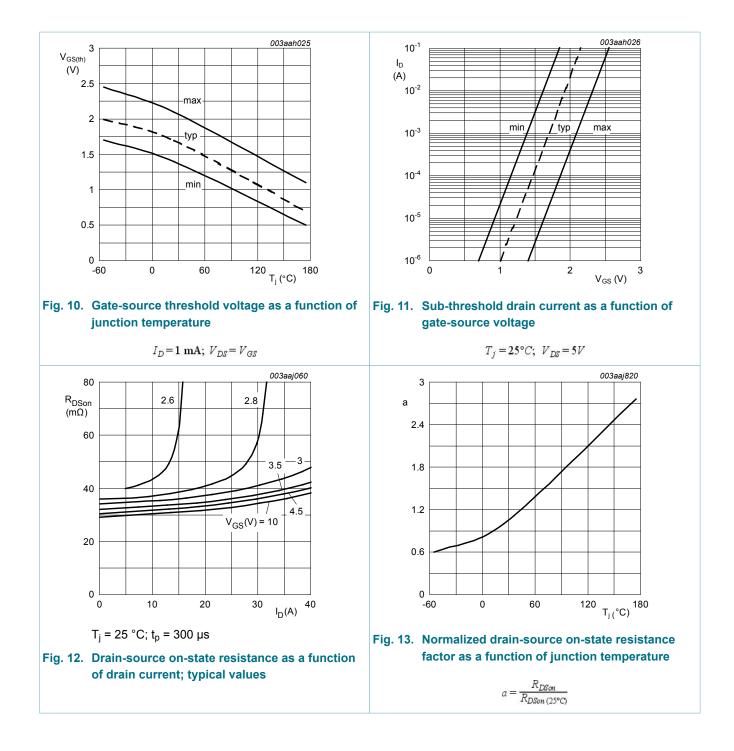
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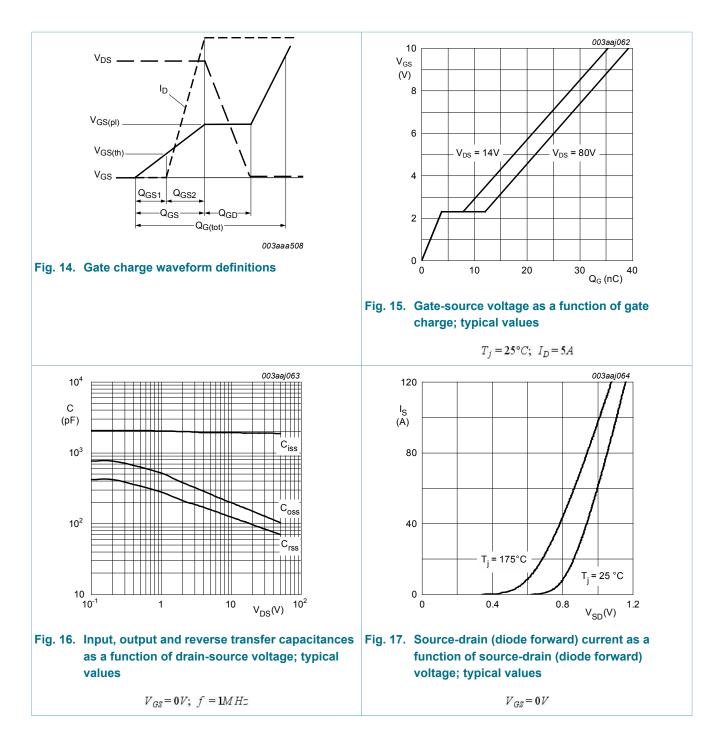
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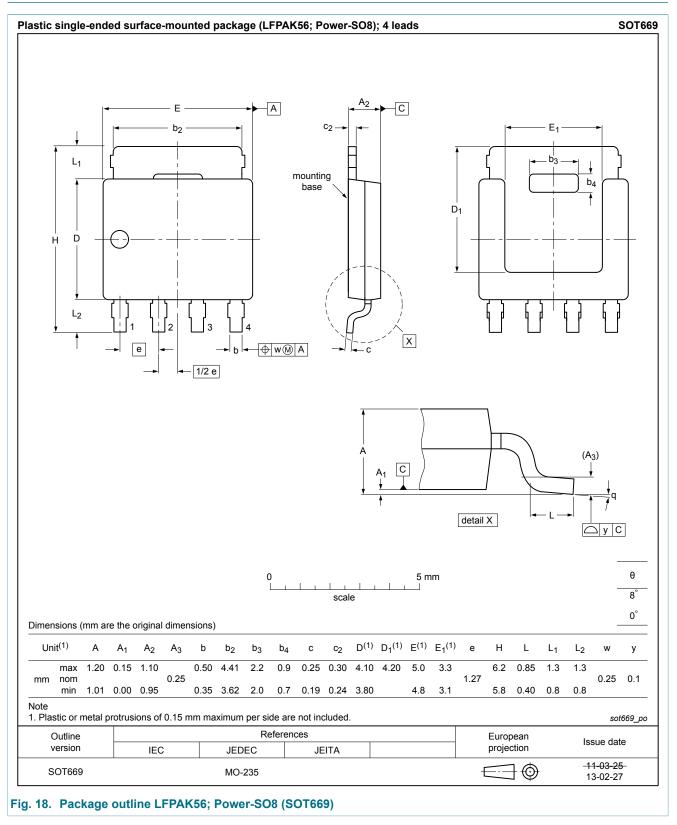


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11. Package outline



PSMN038-100YL

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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